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Renesas Electronics website: http://www.renesas.com

April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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### DATA SHEET



### MOS FIELD EFFECT TRANSISTOR Phase-out/Discontinued 2SJ493

### SWITCHING P-CHANNEL POWER MOS FET INDUSTRIAL USE

#### DESCRIPTION

This product is P-Channel MOS Field Effect Transistor designed for high current switching applications.

#### **ORDERING INFORMATION**

PART NUMBER	PACKAGE			
2SJ493	Isolated TO-220			

#### FEATURES

- Super low on-state resistance  $R_{DS(on)1} = 100 \text{ m}\Omega \text{ (MAX.)} \text{ (VGs} = -10 \text{ V, ID} = -8 \text{ A)}$  $R_{DS(on)2} = 185 \text{ m}\Omega \text{ (MAX.)} \text{ (VGs} = -4 \text{ V, ID} = -8 \text{ A)}$
- Low Ciss: Ciss = 1210 pF (TYP.)
- Built-in gate protection diode

#### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	-60	V
Gate to Source Voltage (VDS = 0 V)	VGSS(AC)	<b>∓ 20</b>	V
Gate to Source Voltage (VDS = $0 \text{ V}$ ) <sup>Note1</sup>	VGSS(DC)	-20, 0	V
Drain Current (DC)	ID(DC)	<b>∓ 16</b>	А
Drain Current (pulse) Note2	D(pulse)	<b>∓ 64</b>	А
Total Power Dissipation (Tc = 25°C)	Рт	30	W
Total Power Dissipation (TA = 25°C)	P⊤	2.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	–55 to +150	°C
Single Avalanche Current Note3	las	-16	А
Single Avalanche Energy <sup>Note3</sup>	Eas	25.6	mJ

#### **Notes 1.** f = 20 kHz, Duty Cycle $\leq 10\%$ (+Side)

- **2.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1 %
- 3. Starting T<sub>ch</sub> = 25 °C, R<sub>A</sub> = 25  $\Omega$ , V<sub>GS</sub> = -20 V  $\rightarrow$  0

#### THERMAL RESISTANCE

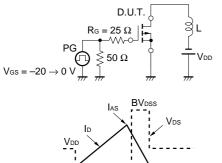
Channel to Case	Rth(ch-C)	4.17	°C/W
Channel to Ambient	Rth(ch-A)	62.5	°C/W

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#### ELECTRICAL CHARACTERISTICS (TA = 25 °C)

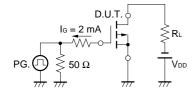
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	RDS(on)1	$V_{GS} = -10 \text{ V}, \text{ Id} = -8 \text{ A}$		70	100	mΩ
	RDS(on)2	$V_{GS} = -4 V, I_D = -8 A$		120	185	mΩ
Gate to Source Cut-off Voltage	V <sub>GS(off)</sub>	$V_{DS} = -10 V$ , $I_{D} = -1 mA$	-1.0	-1.5	-2.0	V
Forward Transfer Admittance	y <sub>fs</sub>	$V_{DS} = -10 \text{ V}, \text{ Id} = -8 \text{ A}$	5.0	11		S
Drain Leakage Current	IDSS	$V_{DS} = -60 V, V_{GS} = 0 V$			-10	μA
Gate to Source Leakage Current	lgss	$V_{GS} = \mp 20 V$ , $V_{DS} = 0 V$			∓ <b>1</b> 0	μA
Input Capacitance	Ciss	V <sub>DS</sub> = -10 V		1210		pF
Output Capacitance	Coss	V <sub>G</sub> s = 0 V		520		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		180		pF
Turn-on Delay Time	td(on)	ID = -8 A		15		ns
Rise Time	tr	$V_{GS(on)} = -10 V$		130		ns
Turn-off Delay Time	td(off)	$V_{DD} = -30 V$		95		ns
Fall Time	tr	Rg = 10 Ω		80		ns
Total Gate Charge	Q <sub>G</sub>	ID = -16 A		42		nC
Gate to Source Charge	Q <sub>GS</sub>	$V_{DD} = -48 V$		8.0		nC
Gate to Drain Charge	Qgd	Vgs = -10 V		10		nC
Body Diode Forward Voltage	VF(S-D)	IF = 16 A, VGS = 0 V		1.0		V
Reverse Recovery Time	trr	IF = 16 A, VGS = 0 V		120		ns
Reverse Recovery Charge	Qrr	di/dt = 50 A/ $\mu$ s		230		nC

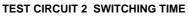
#### TEST CIRCUIT 1 AVALANCHE CAPABILITY

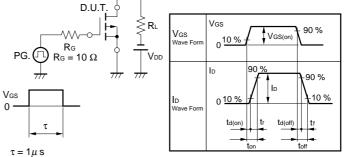


Starting Tch

#### TEST CIRCUIT 3 GATE CHARGE



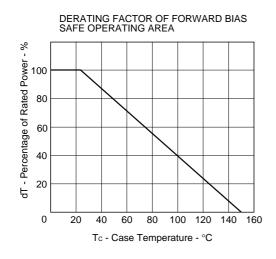




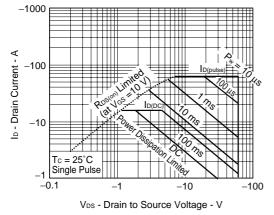




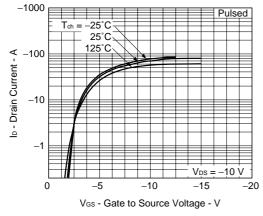
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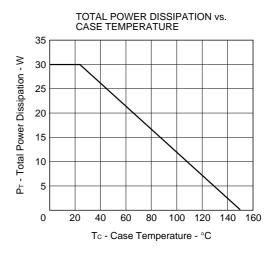




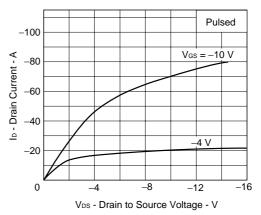


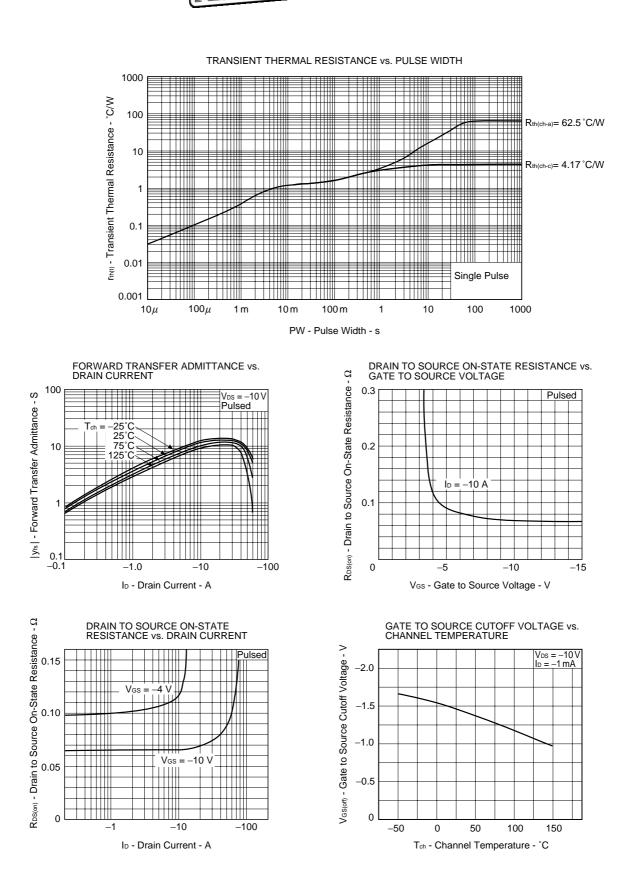






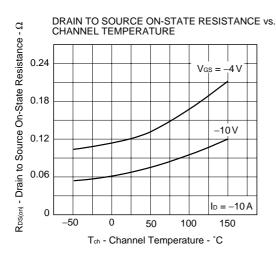


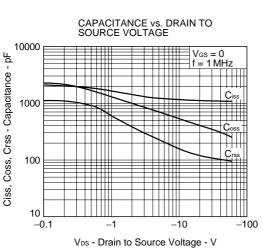


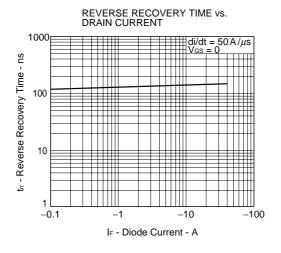


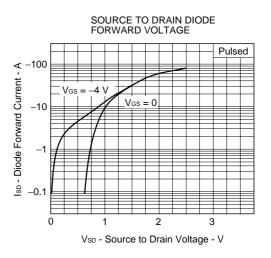
### NEC

# Phase-out/Discontinued

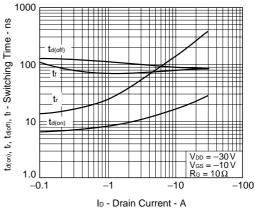


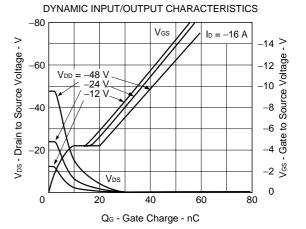




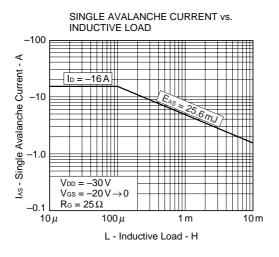


SWITCHING CHARACTERISTICS

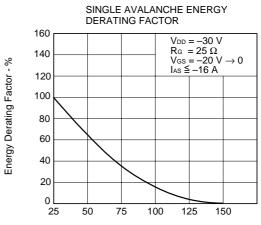




Data Sheet D11265EJ3V0DS00



NEC

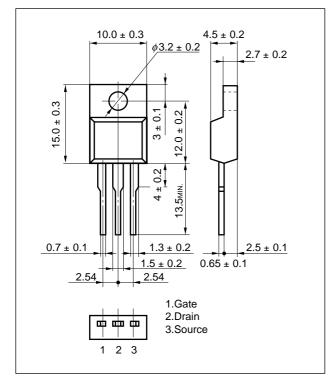


Starting Tch - Starting Channel Temperature - °C

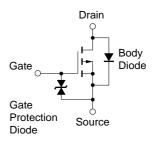
Data Sheet D11265EJ3V0DS00

#### PACKAGE DRAWING (Unit: mm)

Isolated TO-220(MP-45F)



#### EQUIVALENT CIRCUIT



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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